



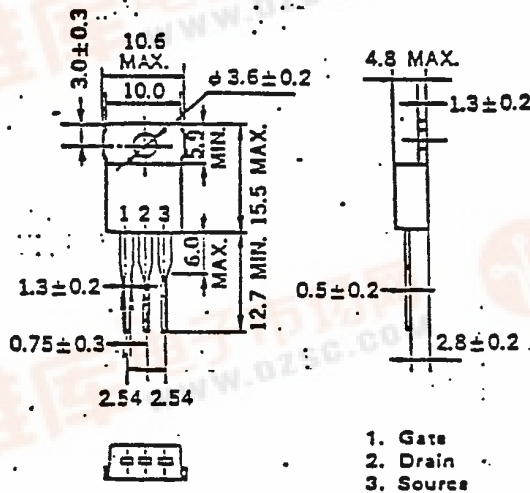
MOS FIELD EFFECT TRANSISTOR

2SJ140

**FAST SWITCHING
P-CHANNEL SILICON POWER MOS FET**

PACKAGE DIMENSIONS

(Unit: mm)



Features

Suitable for switching power supplies, actuator controls and pulse circuits
4V Gate Drive — Logic Level —
Large current switching : $I_D(DC)=19A$
Low $R_{DS(on)}$

No Secondary Breakdown

Absolute Maximum Ratings($T_a=25^\circ C$)

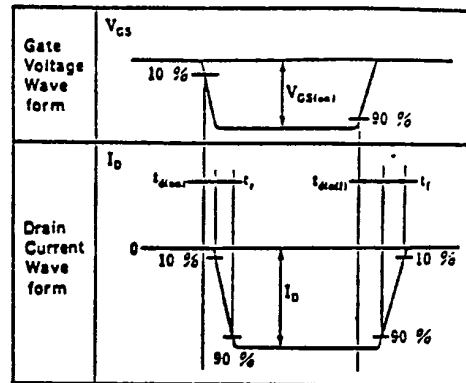
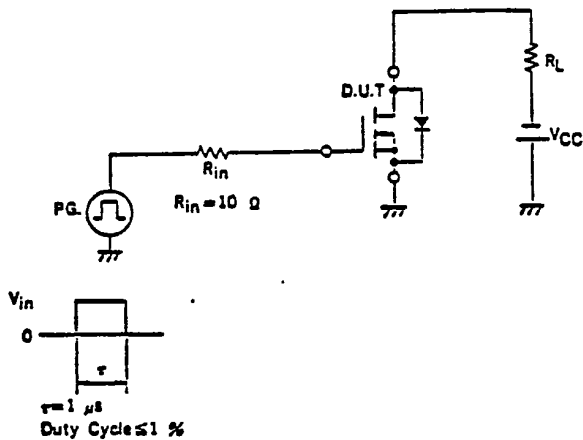
Drain to Source Voltage	V_{DS}	- 60V
Gate to Source Voltage	V_{GS}	$\pm 20V$
Continuous Drain Current	$I_D(DC)$	$\pm 19A$
Pulse Drain Current	$I_D(pulse)$	$\pm 76A$
Total Power Dissipation	P_T	1.5W
Total Power Dissipation	P_{T*}	60W
Channel Temperature	T_{ch}	150 °C
Storage Temperature	T_{stg}	-55to+150 °C
	*	$T_{ch} \leq 150^\circ C$
	**	$T_c=25^\circ C$

Electrical Characteristics ($T_a=25^\circ C$)

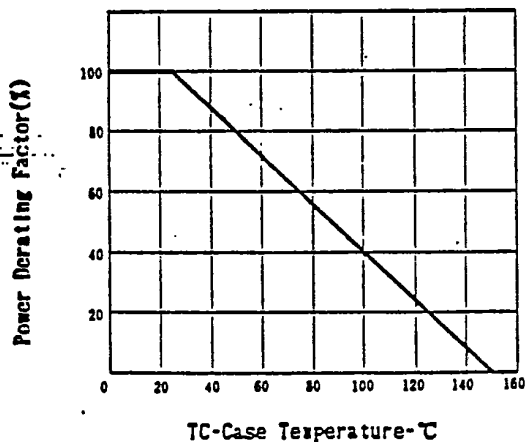
Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain Leakage Current	I_{DSS}			- 10	μA	$V_{DS}=-60V, V_{GS}=0$
Gate to Source Leakage Current	I_{GSS}			100	nA	$V_{GS}=20V, V_{DS}=0$
Gate to Source Cutoff Voltage	$V_{GS(off)}$	-1.0		-3.0	V	$V_{DS}=-10V, I_D=-1.0mA$
Forward Transfer Admittance	$ y_{fs} $	5.0			S	$V_{DS}=-10V, I_D=-10A$
Drain to Source On-State Resistance	$R_{DS(on)}$			0.2	Ω	$V_{GS}=-10V, I_D=-10A$
Drain to Source On-State Resistance	$R_{DS(on)}$			0.4	Ω	$V_{GS}=-4.0V, I_D=-3.0A$
Input Capacitance	C_{iss}		2600		pF	$V_{DS}=-10V,$ $V_{GS}=0,$
Output Capacitance	C_{oss}		630		pF	$f=1.0MHz$
Reverse Transfer Capacitance	C_{rss}		130		pF	$I_D=-10A,$ $V_{GS(on)}=-10V,$
Turn-On Delay Time	$t_d(on)$		20		ns	$V_{cc}=-30V,$ $RL=3\Omega$
Rise Time	t_r		160		ns	
Turn-Off Delay Time	$t_d(off)$		80		ns	
Fall Time	t_f		90		ns	



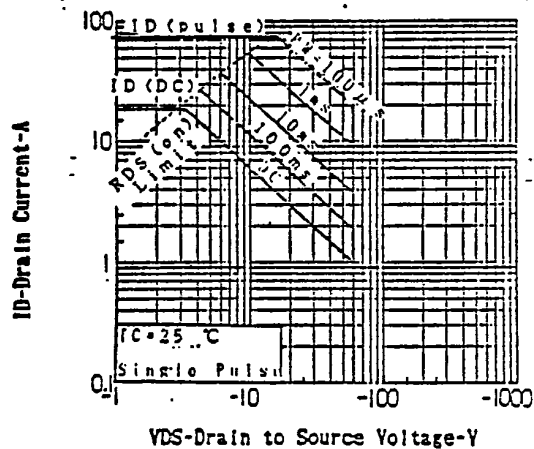
TURN-ON AND TURN-OFF TIME TEST CIRCUIT



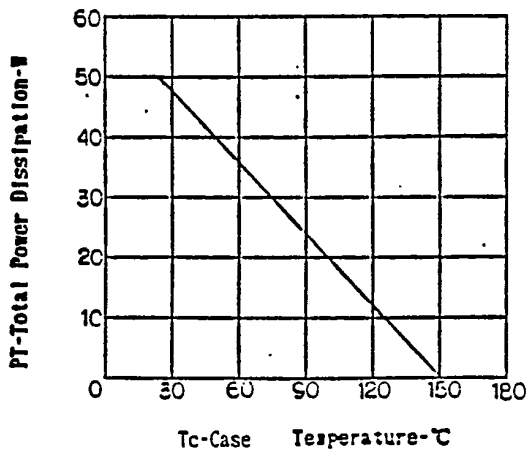
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



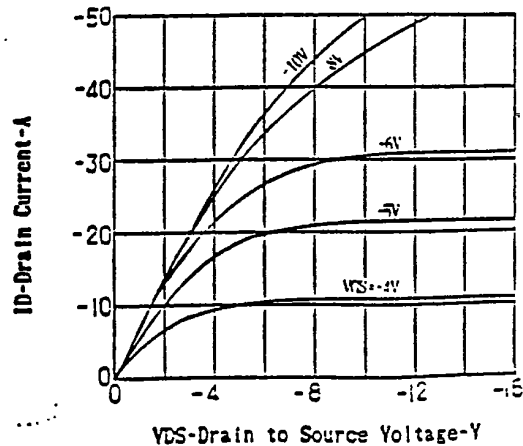
FORWARD BIAS SAFE OPERATING AREA

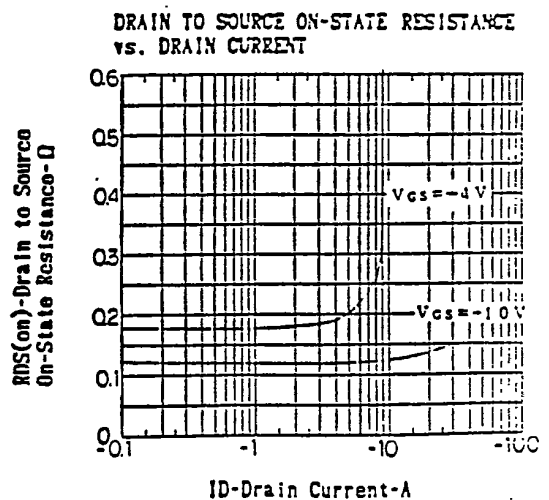
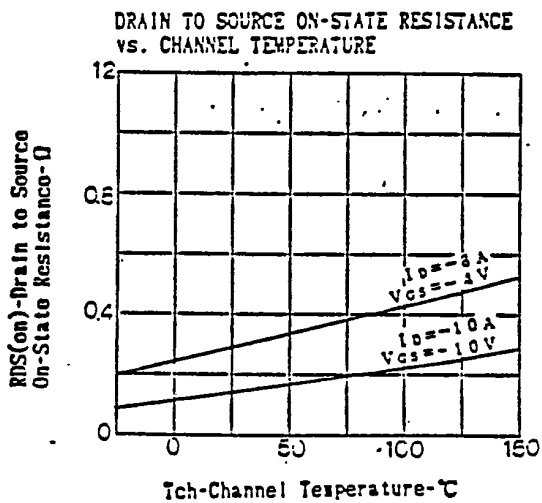
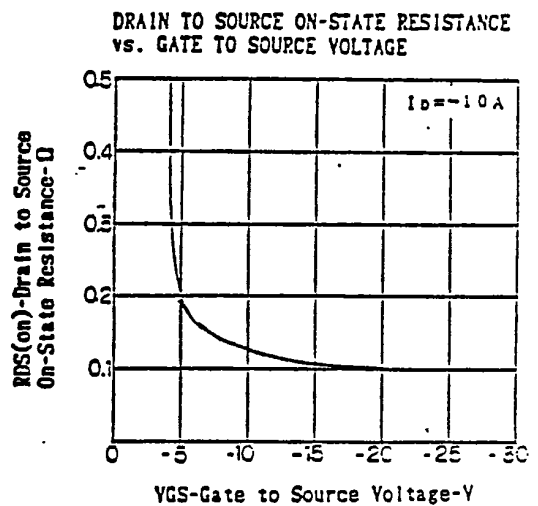
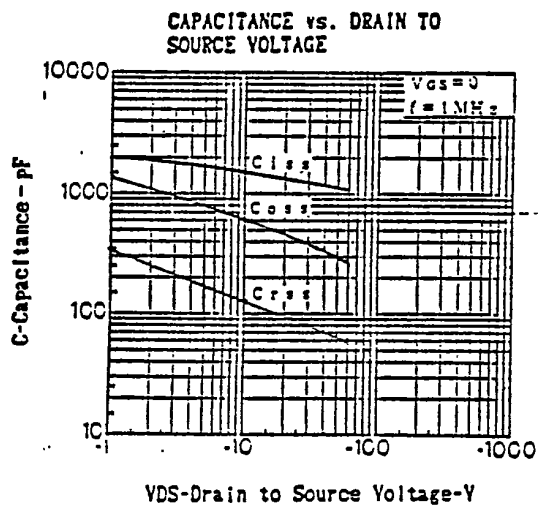
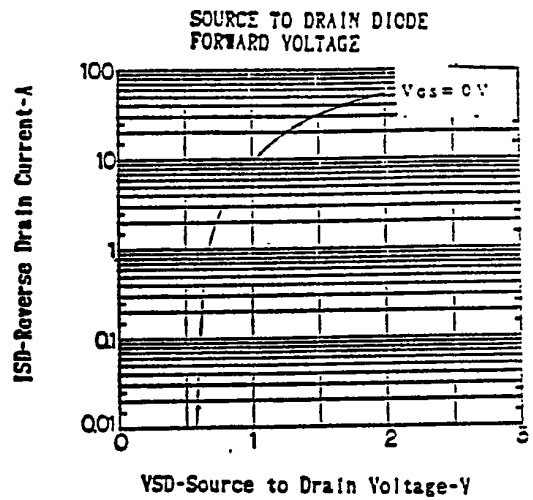
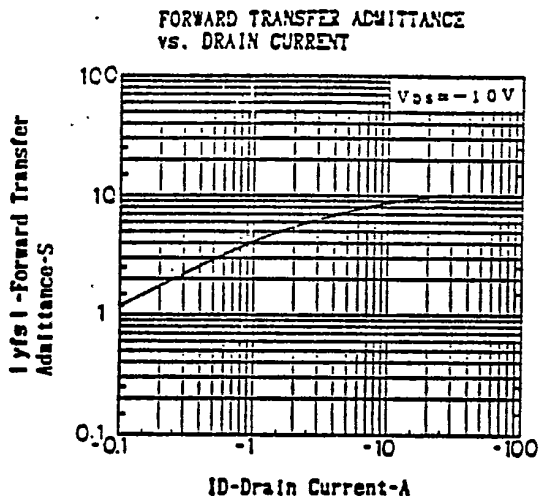


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

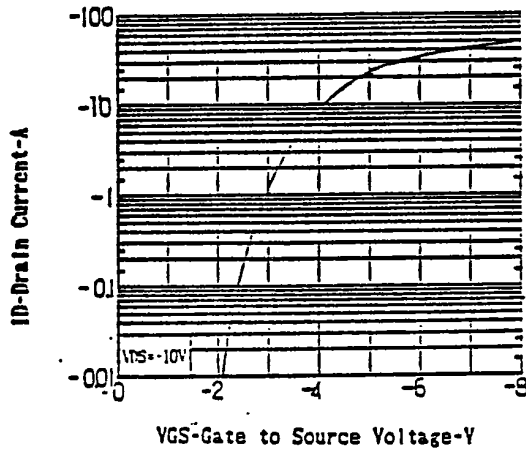


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

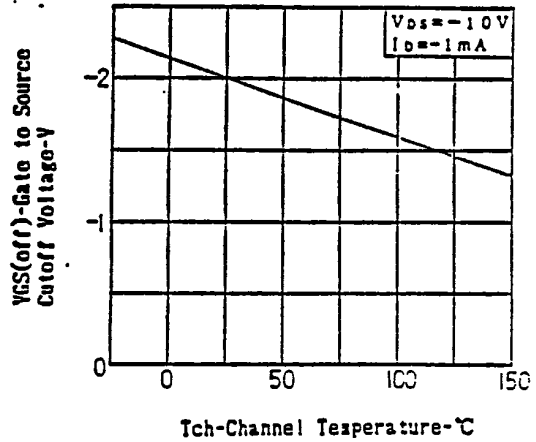




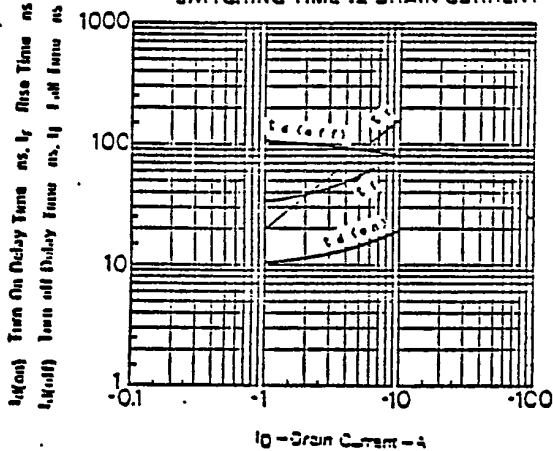
TRANSFER CHARACTERISTICS



GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



SWITCHING TIME vs. DRAIN CURRENT



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